To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SA2081

Silicon PNP Epitaxial

RENESAS

ADE-208-1477 (Z)

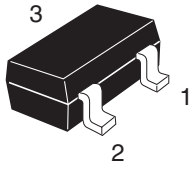
Rev.0
Feb. 2002

Features

- Low frequency amplifier

Outline

CMPAK



1. Emitter
2. Base
3. Collector

Absolute Maximum Ratings

(Ta = 25 °C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	–55	V
Collector to emitter voltage	V_{CEO}	–55	V
Emitter to base voltage	V_{EBO}	–5	V
Collector current	I_C	–100	mA
Collector power dissipation	P_C*	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

*Value on the glass epoxy board (10 mm x 10 mm x 0.7 mm)

Electrical Characteristics

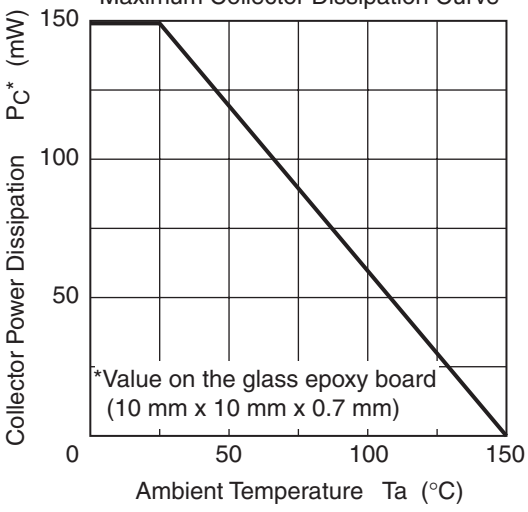
(Ta = 25 °C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	–55	—	—	V	I_C = –10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	–55	—	—	V	I_C = –1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	–5	—	—	V	I_E = –10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	–0.5	µA	V_{CB} = –30 V, I_E = 0
Emitter cutoff current	I_{EBO}	—	—	–0.5	µA	V_{EB} = –2 V, I_C = 0
DC current transfer ratio	h_{FE}*[1]	160	—	800	—	V_{CE} = –12 V, I_C = –2 mA
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	–0.5	V	I_C = –10 mA, I_B = –1 mA
Base to emitter voltage	V_{BE}	—	—	–0.75	V	V_{CE} = –12 V, I_C = –2 mA

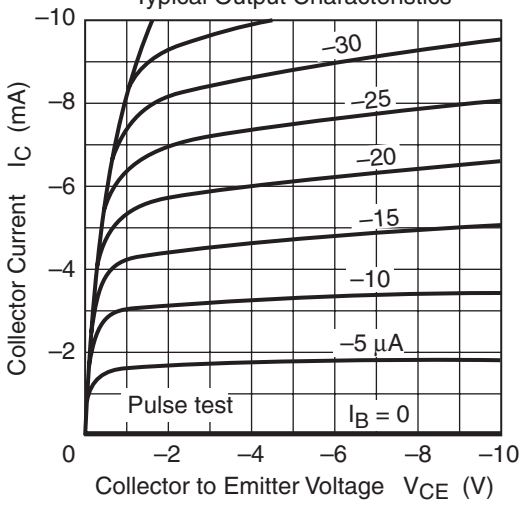
Notes: 1. The 2SA2081 is grouped by h_{FE} as follows.

Grade	C	D	E
Mark	CC	CD	CE
h_{FE}	160 to 320	250 to 500	400 to 800

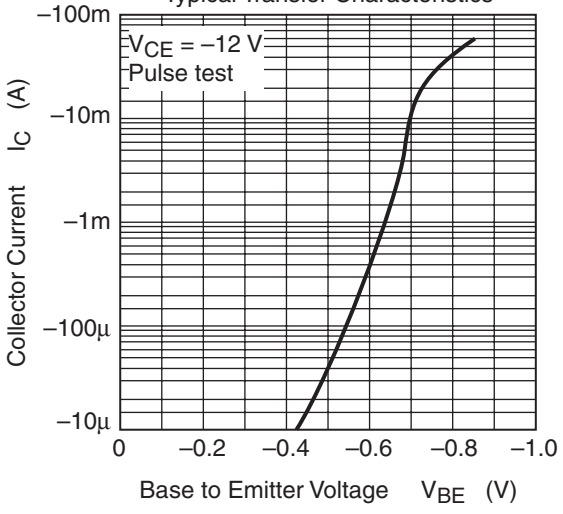
Maximum Collector Dissipation Curve



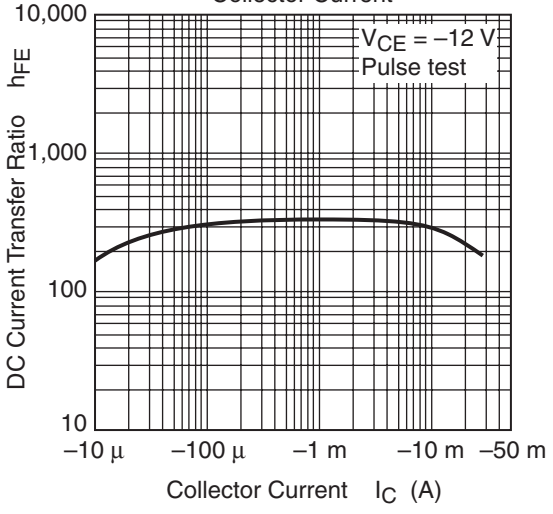
Typical Output Characteristics

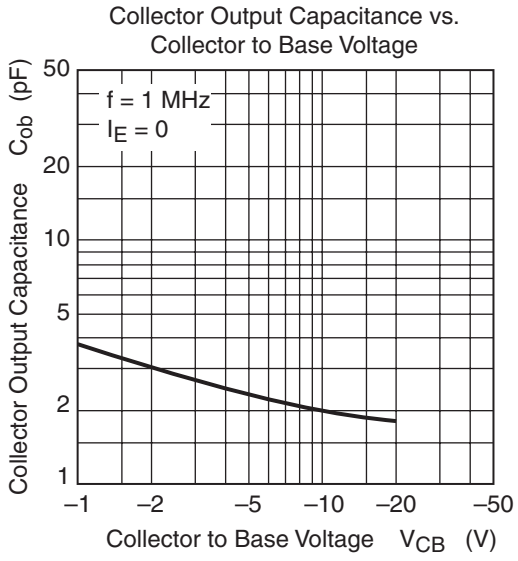


Typical Transfer Characteristics



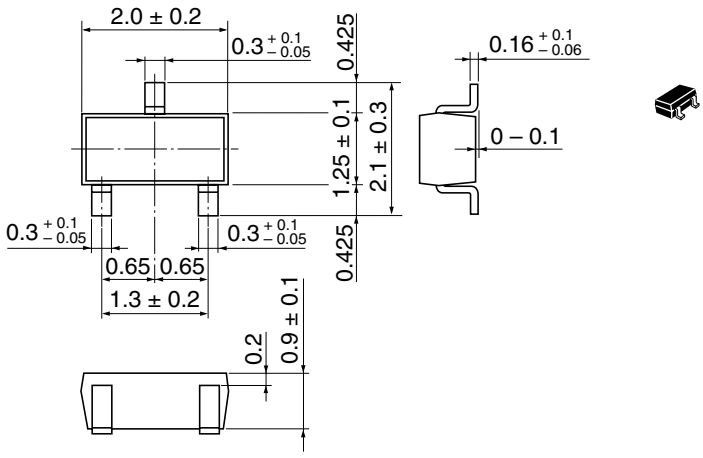
DC Current Transfer Ratio vs. Collector Current




Collector Output Capacitance vs.
Collector to Base Voltage
f = 1 MHz
I_E = 0
Collector Output Capacitance C_{ob} (pF)
50
20
10
5
2
1
–1
–2
–5
–10
–20
–50
Collector to Base Voltage V_{CB} (V)

Package Dimensions

As of July, 2001
Unit: mm



Hitachi Code	CMPAK
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.006 g

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